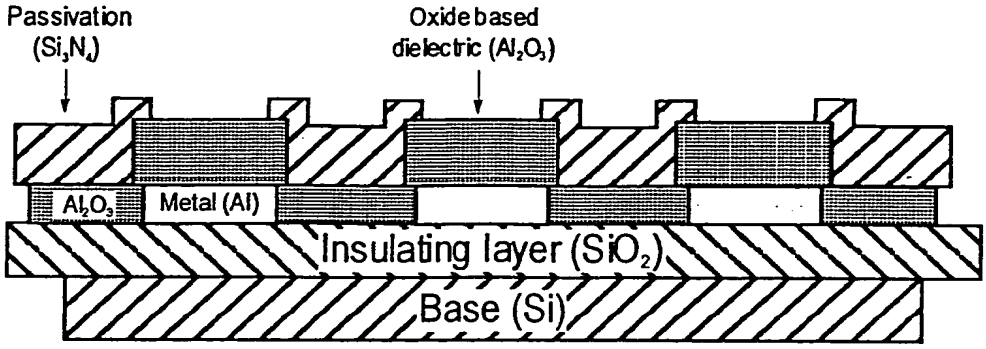

Passivation
(Si_3N_4)
Oxide based
dielectric (Al_2O_3)
Al_2O_3
Metal (Al)
Insulating layer (SiO_2)
Base (Si)

FIG.1

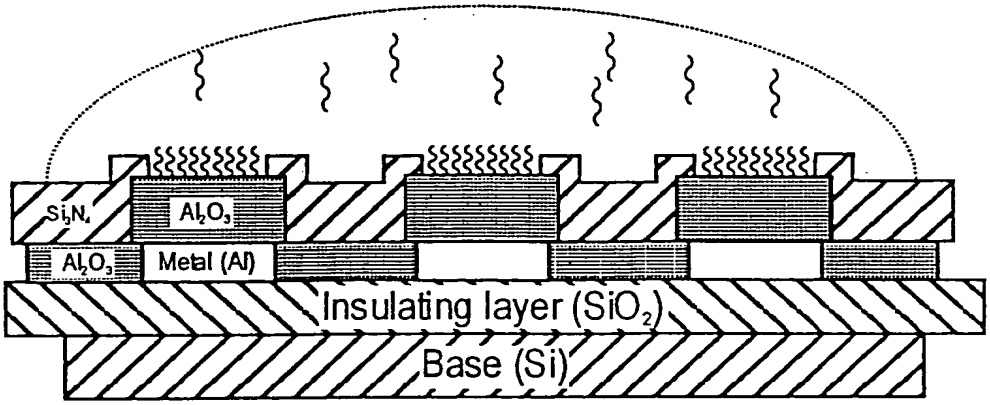

Si_3N_4
Al_2O_3
Al_2O_3
Metal (Al)
Insulating layer (SiO_2)
Base (Si)

FIG.2

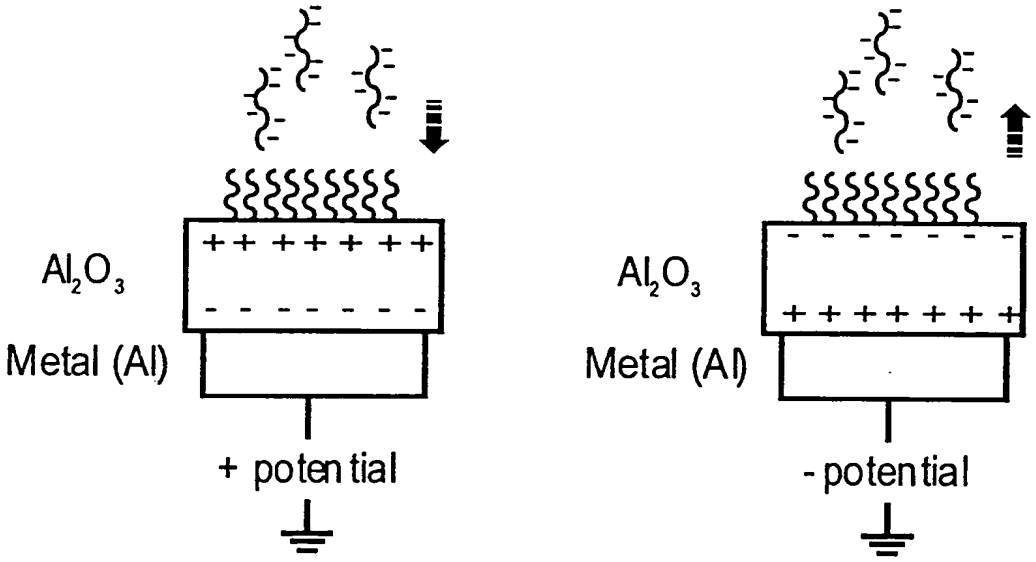


FIG.3

FIG.4

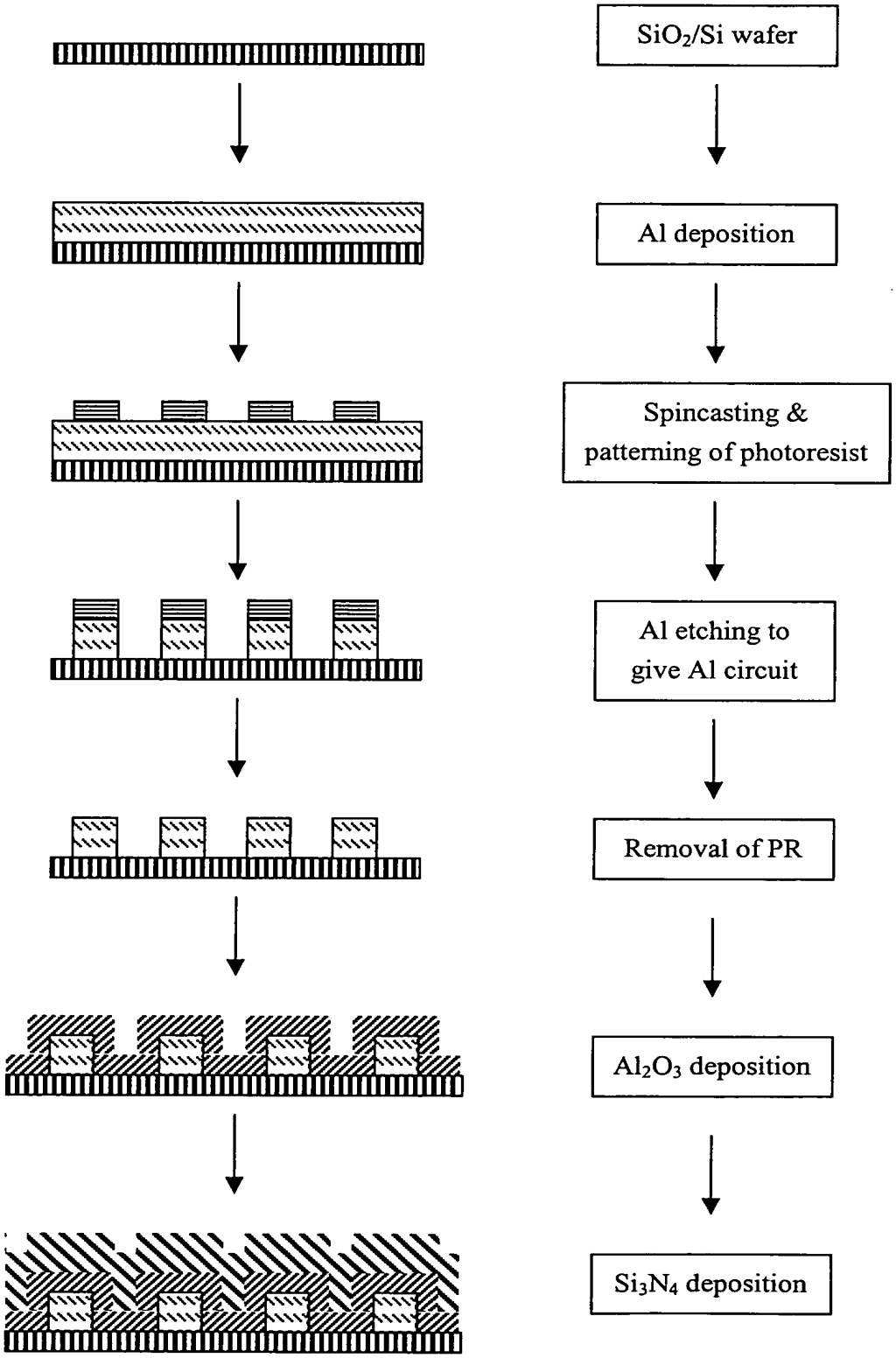

SiO_2/Si wafer
Al deposition
Spincasting & patterning of photoresist
Al etching to give Al circuit
Removal of PR
Al_2O_3 deposition
Si_3N_4 deposition

FIG.4 (cont.)

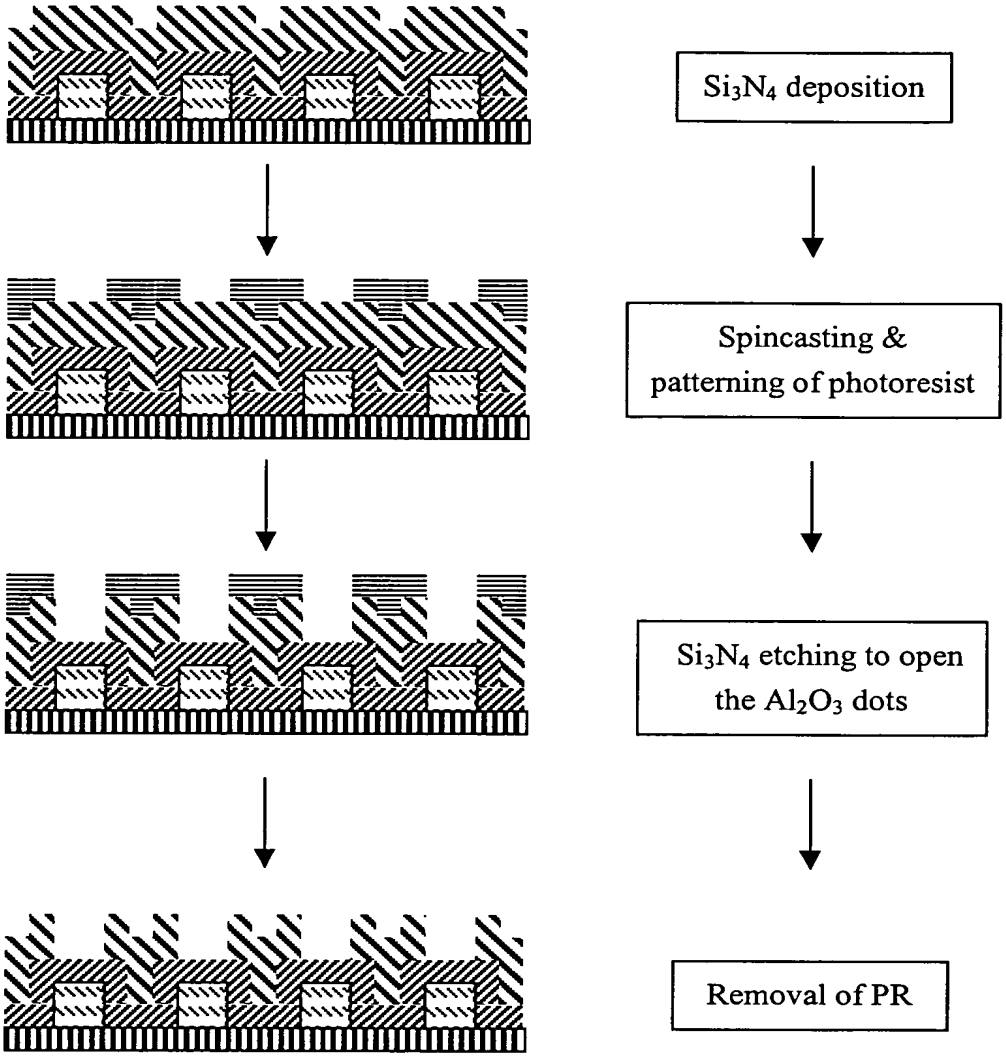
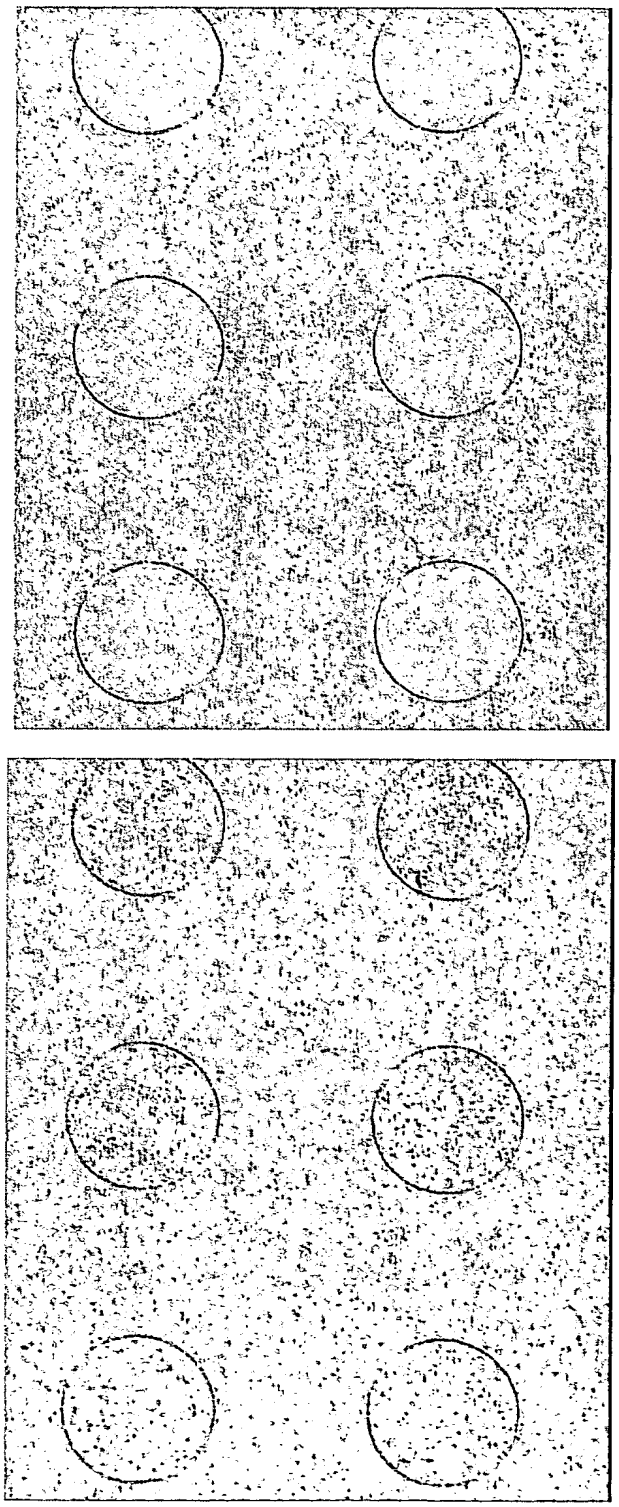

Si_3N_4 deposition
Spincasting & patterning of photoresist
Si_3N_4 etching to open the Al_2O_3 dots
Removal of PR
Final structure
Si_3N_4
Al_2O_3
Al
SiO_2/Si

FIG.5



(b)

(a)

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FIG.6

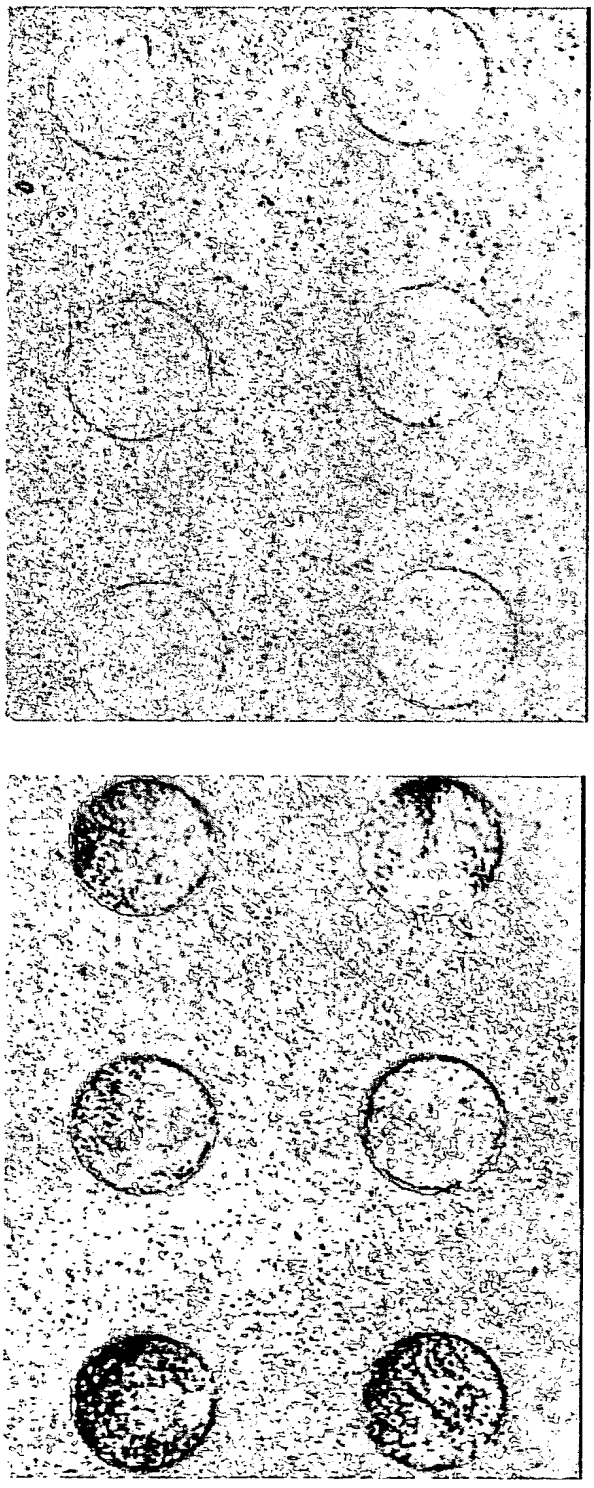

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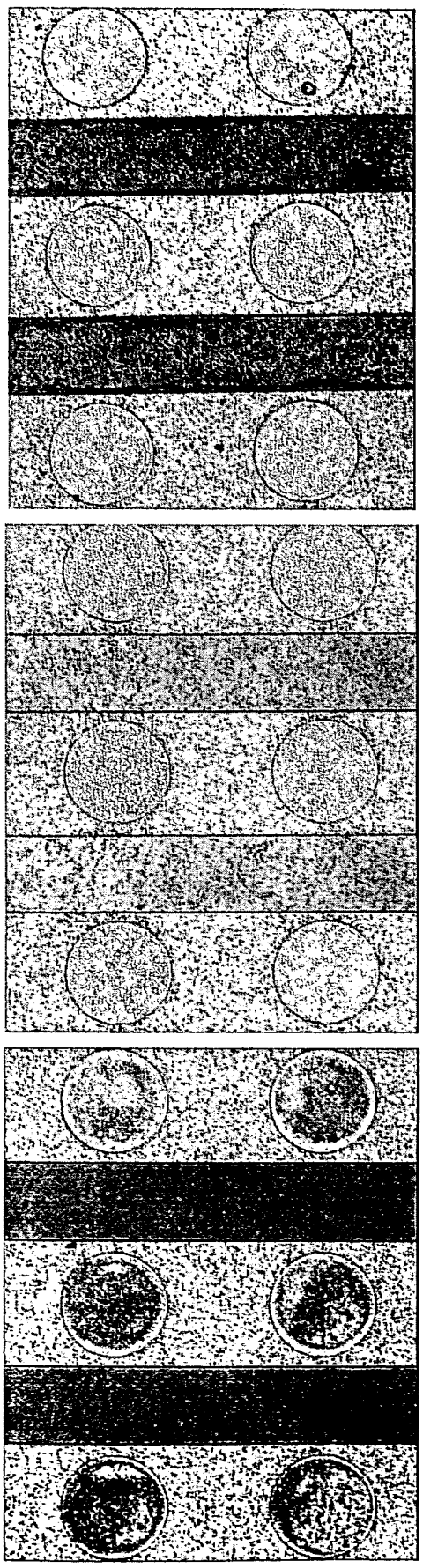
FIG.7



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